

22nd RD50 Workshop (Albuquerque, USA)

Monday 3 June 2013

Session I: Opening & Defect and Material Characterization - Student Union Building (09:00 - 14:00)

-Conveners: Michael Moll

time	[id] title	presenter
09:00	[30] Workshop opening	MOLL, Michael SEIDEL, Sally RUDOLPH, Wolfgang
09:20	[29] Radiation-Induced Trap Spectroscopy in Si Bipolar Transistors and GaAs Diodes	Dr FLEMING, Robert M.
09:50	Coffee Break	
10:20	[9] Studies on n-type silicon after electron irradiation	RADU, Roxana
10:40	[5] Evolution of carrier lifetime characteristics in Si structures during and post-irradiated by neutrons and protons	Prof. VAITKUS, Juozas
11:00	[2] Radiation damage induced by 800 MeV protons in silicon pad diodes	SAGIR, Sinan
11:20	[32] Systematic investigation of p-irradiated Micron pad detectors of different silicon materials	NEUGEBAUER, Hannes
11:40	[25] Extraction of electric field of non-irradiated microstrip detectors using the edge-TCT technique	FERNANDEZ GARCIA, Marcos
12:00	[31] Discussion on Defects and Material Characterization	MOLL, Michael
12:30	Lunch	